## 1. General description

NPN/NPN general-purpose transistor in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: BC857QAS.

NPN/PNP complement: BC847QAPN.

### 2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Low package height of 0.37 mm

## 3. Applications

- General-purpose switching and amplification
- Mobile applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	45	V
I <sub>C</sub>	collector current		-	-	100	mA
Per transistor						,
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C	200	-	450	





45 V, 100 mA NPN/NPN general-purpose transistor

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		6 5 4
2	B1	base TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	Tr. 100
3	C2	collector TR2	[2] [5]	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	3 4	1 2 3
6	C1	collector TR1	Transparent top view	sym020
7	C1	collector TR1	DFN1010B-6 (SOT1216)	
8	C2	collector TR2		

# 6. Ordering information

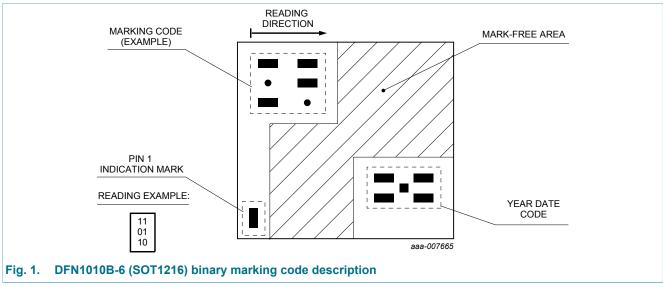
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BC847QAS	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BC847QAS	00 01 00



BC847QAS

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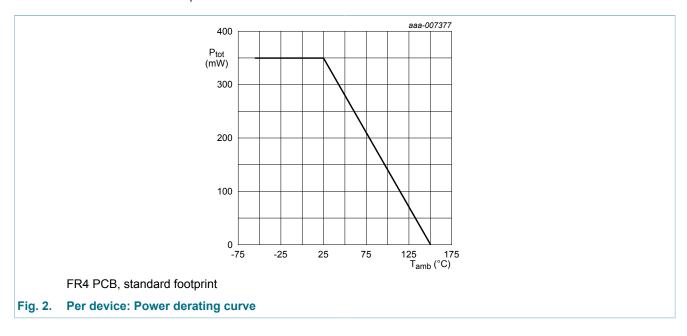
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	'	1			
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
I <sub>BM</sub>	peak base current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	230	mW
Per device					'	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor		,				
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device	,						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

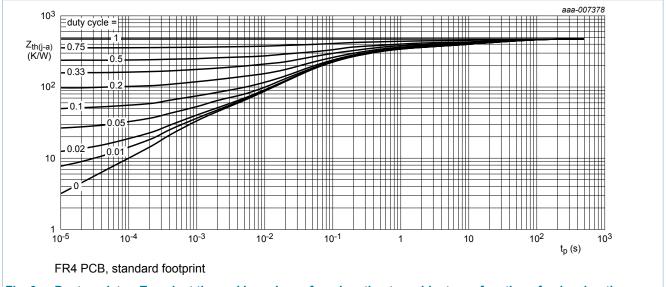


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

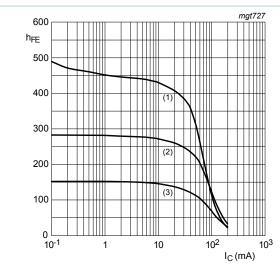
## 45 V, 100 mA NPN/NPN general-purpose transistor

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
Per transis	tor						
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = 30 V; $I_{E}$ = 0 A; $T_{j}$ = 150 °C		-	-	5	μA
	current	$V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	15	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$	:	200	-	450	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C	-	•	-	100	mV
	saturation voltage	$I_{C}$ = 100 mA; $I_{B}$ = 5 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C		-	-	300	mV
V <sub>BEsat</sub> base-emitter saturation voltage	base-emitter saturation	$I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C		-	760	-	mV
	$I_C$ = 100 mA; $I_B$ = 5 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-	900	-	mV	
$V_{BE}$	base-emitter voltage	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 \text{ °C}$	(	600	660	725	mV
		$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	710	820	mV
C <sub>C</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	4	pF
C <sub>E</sub>	emitter capacitance	$V_{EB}$ = 0.5 V; $I_{C}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	11	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C		100	-	-	MHz
NF	noise figure	$V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ; f = 1 MHz; B = 200 Hz; $T_{amb}$ = 25 °C		-	-	10	dB

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$$V_{CE} = 5 V$$

(1) 
$$T_{amb}$$
 = 150 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 4. DC current gain as a function of collector current; typical values

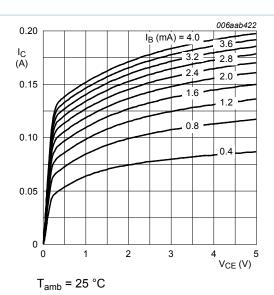
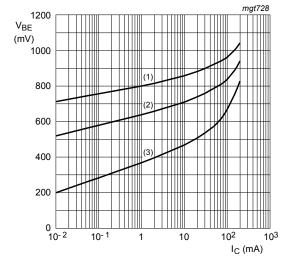


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



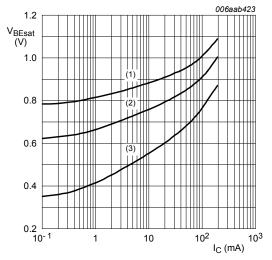
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

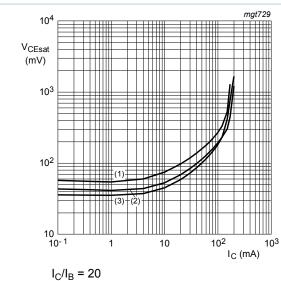
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

### 45 V, 100 mA NPN/NPN general-purpose transistor



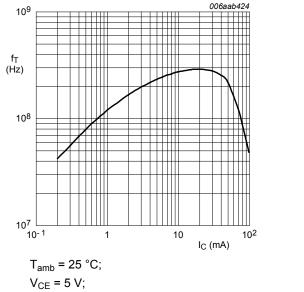
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



f = 100 MHz

Fig. 9. Transition frequency as a function of collector current; typical values

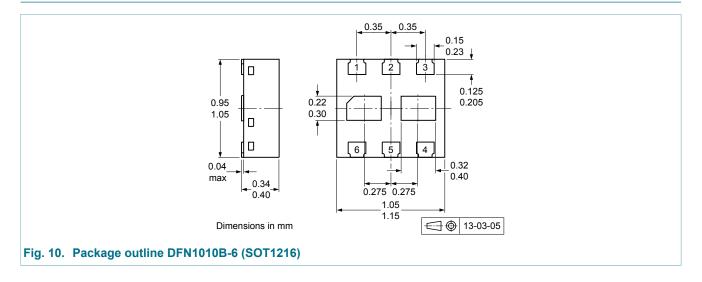
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## 11. Test information

## 11.1 Quality information

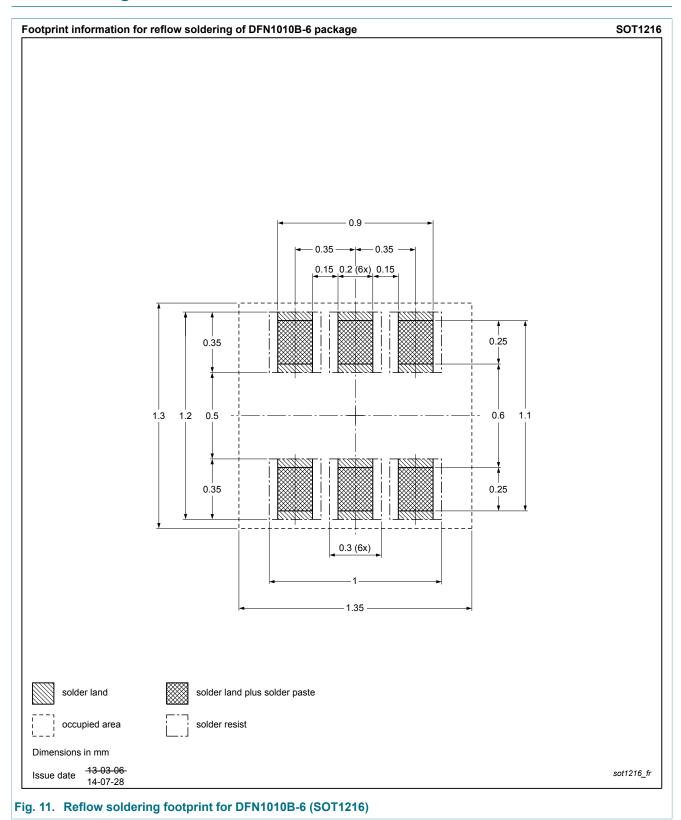
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



45 V, 100 mA NPN/NPN general-purpose transistor

## 13. Soldering



BC847QAS

45 V, 100 mA NPN/NPN general-purpose transistor

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC847QAS v.2	20150708	Product data sheet	-	BC847QAS v.1
Modification:	Change of binary m	arking code position.		
BC847QAS v.1	20140729	Product data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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